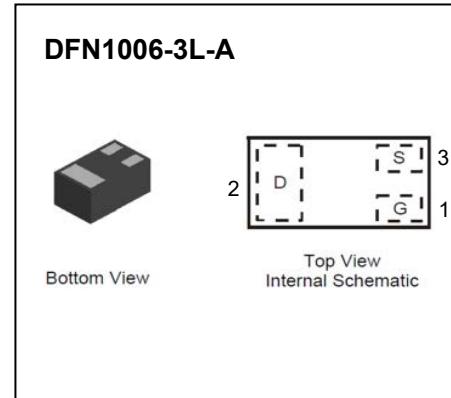


# DFN1006-3L-A Plastic-Encapsulate MOSFETs

## CJBB3134K N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}\text{MAX}$	$I_D$
20V	500m $\Omega$ @4.5V	0.75A
	700m $\Omega$ @2.5V	
	900m $\Omega$ @1.8V	



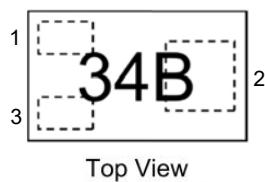
### FEATURE

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low  $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- ESD Protected Gate

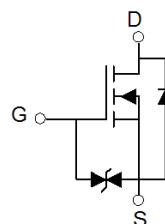
### APPLICATION

- Load/ Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

### MARKING:



### Equivalent Circuit



### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Typical Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current (note 1)	$I_D$	0.75	A
Pulsed Drain Current ( $t_p=10\mu\text{s}$ )	$I_{DM}$	1.8	A
Power Dissipation (note 1)	$P_D$	100	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	1250	°C/W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55~150	°C
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	$T_L$	260	°C

## MOSFET ELECTRICAL CHARACTERISTICS

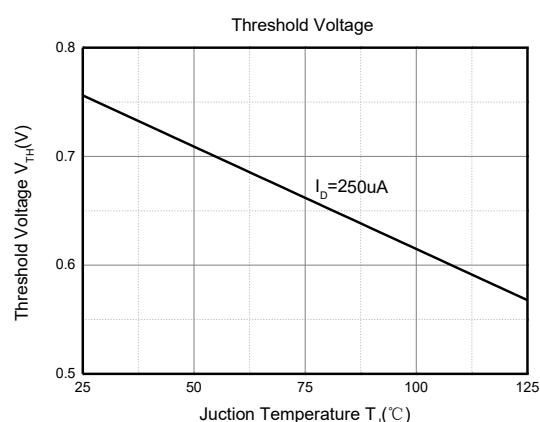
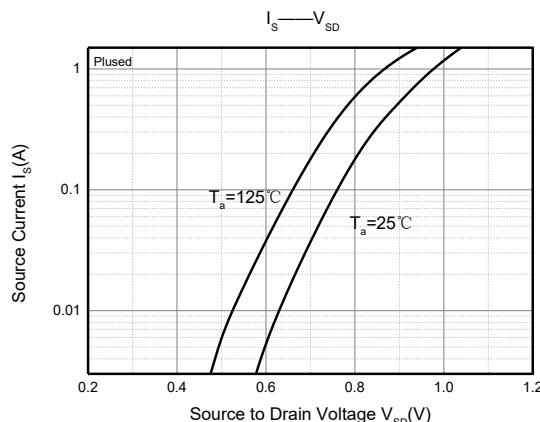
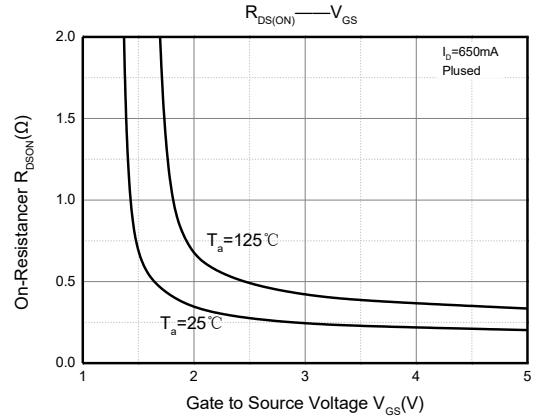
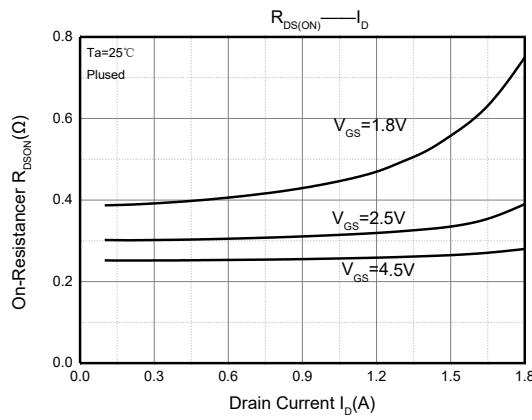
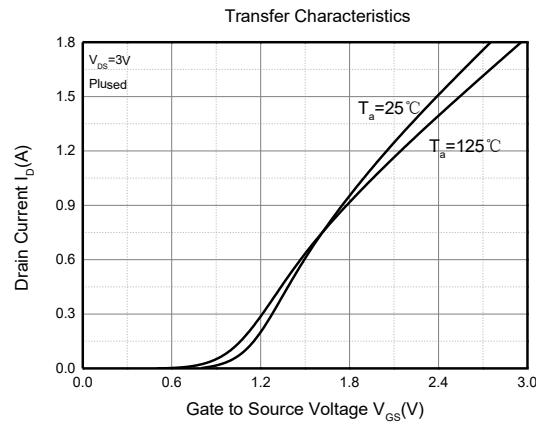
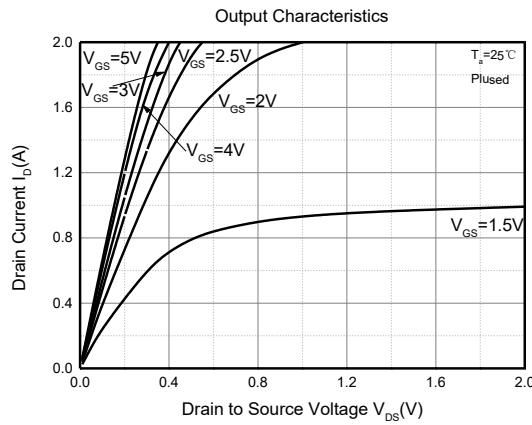
T<sub>a</sub>=25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V			±20	μA
Gate threshold voltage <sup>(2)</sup>	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.35	0.75	1.1	V
Drain-source on-resistance <sup>(2)</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 150mA		250	500	mΩ
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 150mA		300	700	
		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 150mA		370	900	
		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 20mA		460		
		V <sub>GS</sub> = 1.2V, I <sub>D</sub> = 10mA		1200		
Forward transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 150mA	150			mS
<b>Dynamic characteristics<sup>(4)</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, f = 1MHz		79	120	pF
Output Capacitance	C <sub>oss</sub>			13	20	
Reverse Transfer Capacitance	C <sub>rss</sub>			9	15	
<b>Switching Characteristics<sup>(4)</sup></b>						
Turn-on delay time <sup>(3)</sup>	t <sub>d(on)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 500mA, V <sub>GS</sub> = 4.5V, R <sub>G</sub> = 10Ω		6.7		ns
Turn-on rise time <sup>(3)</sup>	t <sub>r</sub>			4.8		
Turn-off delay time <sup>(3)</sup>	t <sub>d(off)</sub>			17.3		
Turn-off fall time <sup>(3)</sup>	t <sub>f</sub>			7.4		
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage <sup>(3)</sup>	V <sub>DS</sub>	I <sub>S</sub> = 0.15A, V <sub>GS</sub> = 0V			1.2	V

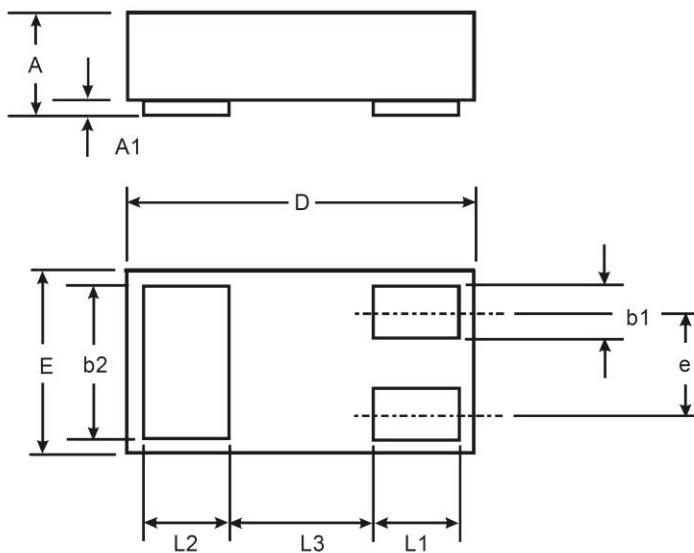
### Notes:

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300μs, Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producting.

## Typical Characteristics



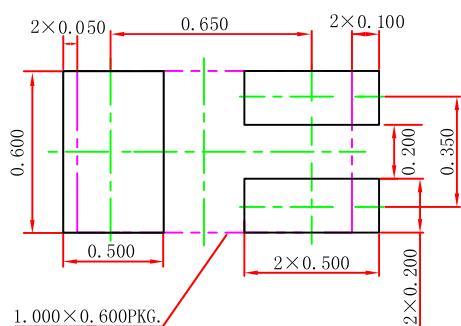
## DFN1006-3L-A Package Outline Dimensions



DFN1006-3L-A			
Dim	Min.	Max.	Typ.
A	0.34	0.40	0.37
A1	0.00	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40

All Dimensions in mm

## DFN1006-3L-A Suggested Pad Layout



### Note:

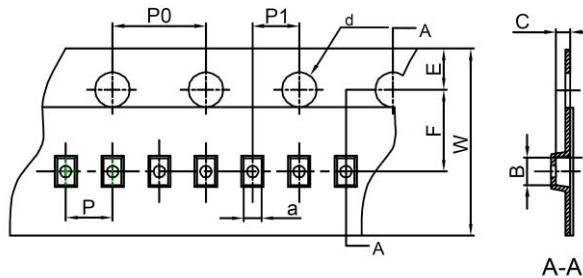
1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.050\text{mm}$ .
3. The pad layout is for reference purposes only.

### NOTICE

JSCJ reserves the right to make modifications,enhancements,improvements,corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

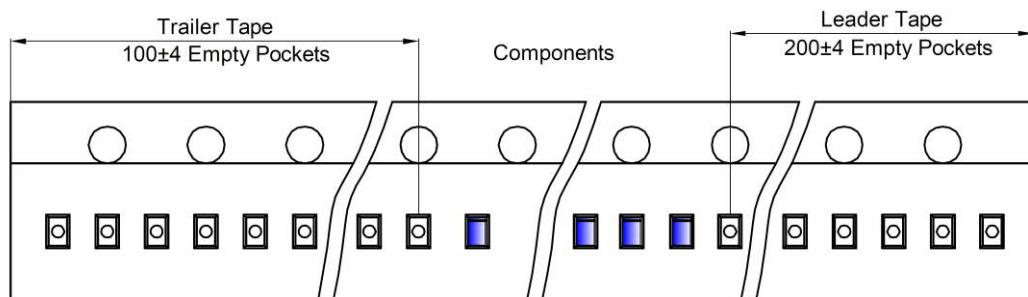
## DFN1006-3L-A Tape and Reel

### DFN1006-3L-A Embossed Carrier Tape

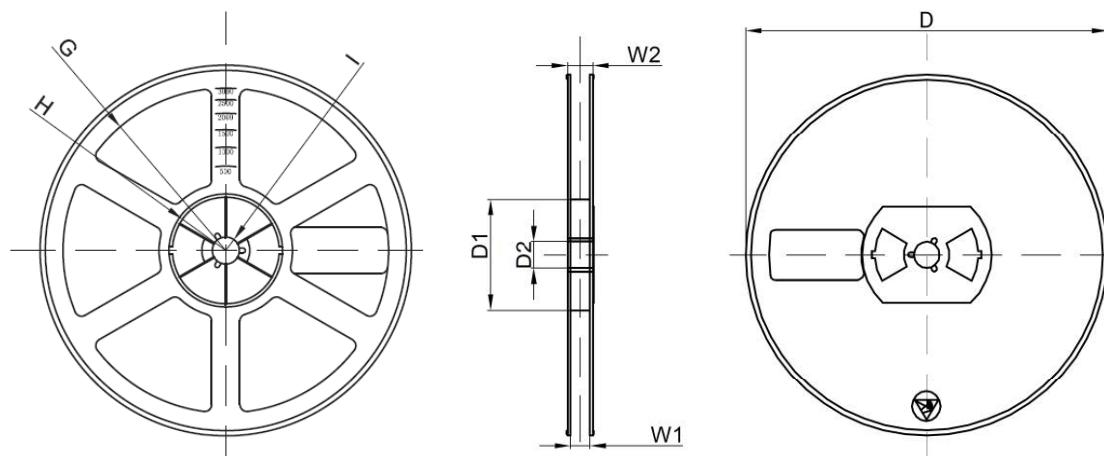


Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFN1006-3L-A	0.66	1.15	0.66	Ø1.50	1.75	3.50	4.00	2.00	2.00	8.00

### DFN1006-3L-A Tape Leader and Trailer



### DFN1006-3L-A Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
10000 pcs	7 inch	100,000 pcs	203×203×195	400,000 pcs	438×438×220	